# 74ABT125

Quad buffer; 3-state

Rev. 6 — 3 November 2011

Product data sheet

#### 1. **General description**

The 74ABT125 high-performance BiCMOS device combines low static and dynamic power dissipation with high speed and high output drive.

The 74ABT125 device is a quad buffer that is ideal for driving bus lines. The device features four Output Enables (1OE, 2OE, 3OE, 4OE), each controlling one of the 3-state outputs.

#### **Features and benefits** 2.

- Quad bus interface
- 3-state buffers
- Live insertion and extraction permitted
- Output capability: HIGH –32 mA; LOW +64 mA
- Power-up 3-state
- Inputs are disabled during 3-state mode
- Latch-up protection exceeds 500 mA per JESD78 class II level A
- ESD protection:
  - HBM JESD22-A114E exceeds 2000 V
  - ♦ MM JESD22-A115-A exceeds 200 V

#### **Ordering information** 3.

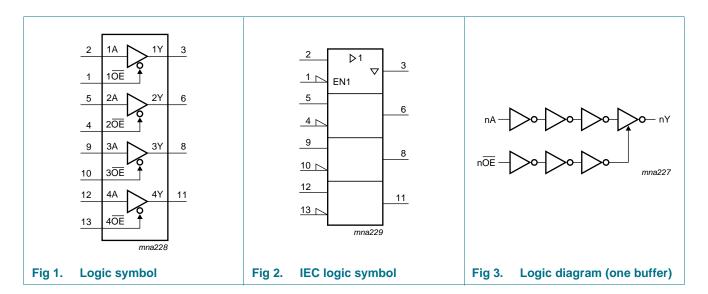
Table 1. **Ordering information** 

Type number	Package									
	Temperature range	Name	Description	Version						
74ABT125N	−40 °C to +85 °C	DIP14	plastic dual in-line package; 14 leads (300 mil)	SOT27-1						
74ABT125D	−40 °C to +85 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1						
74ABT125DB	–40 °C to +85 °C	SSOP14	plastic shrink small outline package; 14 leads; body width 5.3 mm	SOT337-1						
74ABT125PW	–40 °C to +85 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1						
74ABT125BQ	–40 °C to +85 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 $\times$ 3 $\times$ 0.85 mm	SOT762-1						



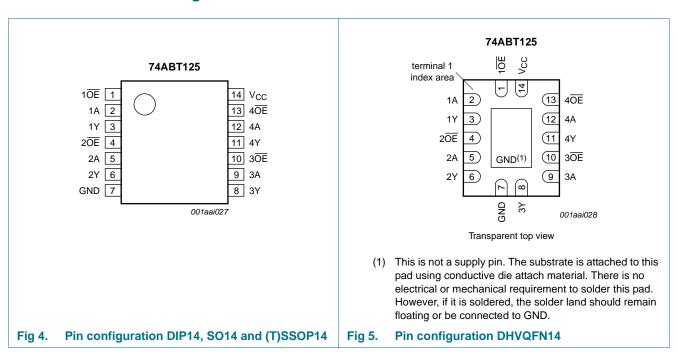
Quad buffer; 3-state

## 4. Functional diagram



## 5. Pinning information

### 5.1 Pinning



### 5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1OE to 4OE	1, 4, 10, 13	output enable input (active LOW)
1A to 4A	2, 5, 9, 12	data input
1Y to 4Y	3, 6, 8, 11	data output
GND	7	ground (0 V)
V <sub>CC</sub>	14	supply voltage

## 6. Functional description

Table 3. Function selection[1]

Inputs nOE	Output	
nOE	nA	nY
L	L	L
L	Н	Н
Н	X	Z

<sup>[1]</sup> H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

# 7. Limiting values

Table 4. Limiting values[1]

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+7.0	V
VI	input voltage		-1.2	+7.0	V
Vo	output voltage	output in OFF-state or HIGH-state	-0.5	+5.5	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < 0 V	-18	-	mA
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < 0 V	-50	-	mA
Io	output current	output in LOW-state	-	128	mA
Tj	junction temperature		[2] _	150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } +85  ^{\circ}\text{C}$	<u>[3]</u> _	500	mW

<sup>[1]</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

<sup>[2]</sup> The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability.

<sup>[3]</sup> SO14 packages: above 70 °C P<sub>tot</sub> derate linearly with 8 mW/K SSOP14 and TSSOP20 packages: above 60 °C P<sub>tot</sub> derate linearly with 5.5 mW/K DHVQFN14 packages: above 60 °C P<sub>tot</sub> derate linearly with 4.5 mW/K

## Quad buffer; 3-state

# 8. Recommended operating conditions

Table 5. Operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		4.5	5.5	V
VI	input voltage		0	$V_{CC}$	V
$V_{IH}$	HIGH-level input voltage		2.0	-	V
$V_{IL}$	LOW-level Input voltage		-	0.8	V
I <sub>OH</sub>	HIGH-level output current		-32	-	mA
I <sub>OL</sub>	LOW-level output current		-	64	mA
Δt/ΔV	input transition rise and fall rate		-	10	ns/V
T <sub>amb</sub>	ambient temperature	in free air	-40	+85	°C

# 9. Static characteristics

Table 6. Static characteristics

Symbol	Parameter	Conditions		25 °C			-40 °C t	Unit	
				Min	Тур	Max	Min	Max	
$V_{IK}$	input clamping voltage	$V_{CC} = 4.5 \text{ V}; I_{IK} = -18 \text{ mA}$		-	-0.9	-1.2	-	-1.2	V
$V_{OH}$	HIGH-level output	$V_I = V_{IL}$ or $V_{IH}$							
voltage		$V_{CC} = 4.5 \text{ V}; I_{OH} = -3 \text{ mA}$		2.5	2.9	-	2.5	-	V
		$V_{CC} = 5.0 \text{ V}; I_{OH} = -3 \text{ mA}$		3.0	3.4	-	3.0	-	V
		$V_{CC}$ = 4.5 V; $I_{OH}$ = -32 mA	$I_{CC} = 4.5 \text{ V}; I_{OH} = -32 \text{ mA}$		2.4	-	2.0	-	V
$V_{OL}$	LOW-level output voltage	$V_{CC}$ = 4.5 V; $I_{OL}$ = 64 mA; $V_I$ = $V_{IL}$ or $V_{IH}$	= V <sub>IL</sub> or V <sub>IH</sub>		0.35	0.55	-	0.55	V
I <sub>I</sub>	input leakage current	$V_{CC} = 5.5 \text{ V}; V_{I} = \text{GND or } 5.5 \text{ V}$	$_{\rm C}$ = 5.5 V; V <sub>I</sub> = GND or 5.5 V		±0.01	±1.0	-	±1.0	μΑ
I <sub>OFF</sub>	power-off leakage current	$V_{CC} = 0.0 \text{ V}; \text{ V}_{I} \text{ or V}_{O} \le 4.5 \text{ V}$		-	±5.0	±100	-	±100	μА
I <sub>O(pu/pd)</sub>	power-up/power-down output current	$V_{CC}$ = 2.1 V; $V_O$ = $0.5$ V; $V_I$ = GND or $V_{CC}$ ; $\overline{OE}$ = don't care	[1]	-	±5.0	±50	-	±50	μА
l <sub>OZ</sub>	OFF-state output	$V_{CC} = 5.5 \text{ V}; V_I = V_{IL} \text{ or } V_{IH}$							
	current	V <sub>O</sub> = 2.7 V		-	1.0	50	-	50	μΑ
		V <sub>O</sub> = 0.5 V		-	-1.0	-50	-	-50	μΑ
I <sub>LO</sub>	output leakage current	HIGH-state; $V_O = 5.5 \text{ V}$ ; $V_{CC} = 5.5 \text{ V}$ ; $V_I = \text{GND or } V_{CC}$		-	5.0	50	-	50	μΑ
Io	output current	$V_{CC} = 5.5 \text{ V}; V_O = 2.5 \text{ V}$	[2]	-50	-100	-180	-50	-180	mΑ
I <sub>CC</sub>	supply current	$V_{CC} = 5.5 \text{ V}; V_I = \text{GND or } V_{CC}$							
		outputs HIGH-state		-	65	250	-	250	μΑ
		outputs LOW-state		-	12	15	-	30	mΑ
		outputs disabled		-	65	250	-	50	μΑ

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Table 6. Static characteristics ... continued

Symbol	Parameter	Conditions	Conditions				-40 °C to	o +85 °C	Unit
				Min	Тур	Max	Min	Max	
$\Delta I_{CC}$	additional supply current	per control pin; $V_{CC} = 5.5 \text{ V}$ ; one control input at 3.4 V, other inputs at $V_{CC}$ or GND outputs enabled							
				-	0.5	1.5	-	1.5	mΑ
		outputs disabled		-	50	250	-	250	mΑ
		one enable input at 3.4 V and other inputs at $V_{CC}$ or GND; outputs disabled		-	0.5	1.5	-	1.5	mA
C <sub>I</sub>	input capacitance	$V_I = 0 \text{ V or } V_{CC}$		-	4	-	-	-	pF
Co	output capacitance	outputs disabled; $V_0 = 0 \text{ V or } V_{CC}$		-	7	-	-	-	pF

<sup>[1]</sup> This parameter is valid for any  $V_{CC}$  between 0 V and 2.1 V, with a transition time of up to 10 ms. From  $V_{CC}$  = 2.1 V to  $V_{CC}$  = 5 V  $\pm$  10 %, a transition time of up to 100  $\mu$ s is permitted.

# 10. Dynamic characteristics

Table 7. Dynamic characteristics

GND = 0 V. Test circuit is shown in Figure 8.

Parameter	Conditions		V <sub>CC</sub> =	5.0 V		Unit	
		Min	Тур	Max	Min	Max	
LOW to HIGH propagation delay	nA to nY, see Figure 6	1.0	2.8	4.1	1.0	4.6	ns
HIGH to LOW propagation delay	nA to nY; see Figure 6	1.0	3.1	4.6	1.0	4.9	ns
OFF-state to HIGH propagation delay	nOE to nY; see Figure 7	1.0	3.2	5.0	1.0	5.9	ns
OFF-state to LOW propagation delay	nOE to nY; see Figure 7	1.0	4.2	6.2	1.0	6.8	ns
HIGH to OFF-state propagation delay	nOE to nY; see Figure 7	1.0	4.1	5.4	1.0	6.2	ns
LOW to OFF-state propagation delay	nOE to nY; see Figure 7	1.5	2.8	5.0	1.5	5.5	ns
	LOW to HIGH propagation delay HIGH to LOW propagation delay OFF-state to HIGH propagation delay OFF-state to LOW propagation delay HIGH to OFF-state propagation delay LOW to OFF-state	LOW to HIGH propagation delay  HIGH to LOW propagation delay  OFF-state to HIGH propagation delay  OFF-state to LOW propagation delay  OFF-state to LOW propagation delay  OFF-state to LOW propagation delay  HIGH to OFF-state propagation delay  LOW to OFF-state noe figure 7	LOW to HIGH propagation delay  HIGH to LOW propagation delay  OFF-state to HIGH propagation delay  OFF-state to LOW propagation delay  OFF-state to LOW propagation delay  OFF-state to LOW propagation delay  HIGH to OFF-state propagation delay  LOW to OFF-state noe figure 7  1.0	LOW to HIGH propagation delay  HIGH to LOW propagation delay  OFF-state to HIGH propagation delay  OFF-state to LOW propagation delay  HIGH to OFF-state propagation delay  LOW to OFF-state no     DE to nY; see Figure 7	Min Typ Max  LOW to HIGH propagation delay  HIGH to LOW propagation delay  OFF-state to HIGH propagation delay  OFF-state to LOW propagation delay  HIGH to OFF-state propagation delay  LOW to OFF-state nOE to nY; see Figure 7  1.0 4.1 5.4	V <sub>CC</sub> = 5.0MinTypMaxMinLOW to HIGH propagation delaynA to nY; see Figure 61.02.84.11.0HIGH to LOW propagation delaynA to nY; see Figure 61.03.14.61.0OFF-state to HIGH propagation delayn $\overline{OE}$ to nY; see Figure 71.03.25.01.0OFF-state to LOW propagation delayn $\overline{OE}$ to nY; see Figure 71.04.26.21.0HIGH to OFF-state propagation delayn $\overline{OE}$ to nY; see Figure 71.04.15.41.0LOW to OFF-staten $\overline{OE}$ to nY; see Figure 71.52.85.01.5	V <sub>CC</sub> = 5.0 V $\pm$ 0.5 VMinTypMaxMinMaxLOW to HIGH propagation delaynA to nY; see Figure 61.02.84.11.04.6HIGH to LOW propagation delaynA to nY; see Figure 61.03.14.61.04.9OFF-state to HIGH propagation delayn $\overline{OE}$ to nY; see Figure 71.03.25.01.05.9OFF-state to LOW propagation delayn $\overline{OE}$ to nY; see Figure 71.04.26.21.06.8HIGH to OFF-state propagation delayn $\overline{OE}$ to nY; see Figure 71.04.15.41.06.2LOW to OFF-state propagation delayn $\overline{OE}$ to nY; see Figure 71.52.85.01.55.5

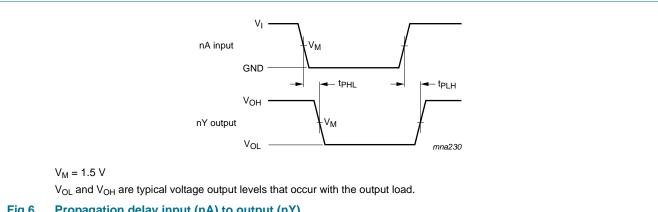
<sup>[2]</sup> Not more than one output should be tested at a time, and the duration of the test should not exceed one second.

<sup>[3]</sup> This is the increase in supply current for each input at 3.4 V.

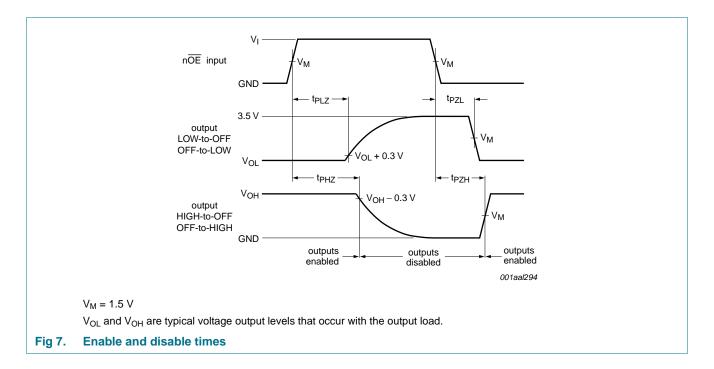
74ABT125 **NXP Semiconductors** 

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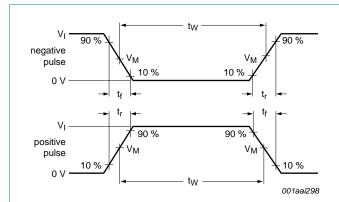
### 11. Waveforms

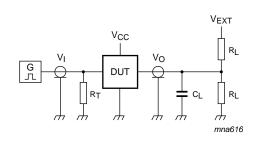






Quad buffer; 3-state





b. Test circuit

#### a. Input pulse definition

Test data is given in Table 8.

Test circuit definitions:

 $R_L$  = Load resistance.

C<sub>L</sub> = Load capacitance including jig and probe capacitance.

 $R_T$  = Termination resistance should be equal to output impedance  $Z_0$  of the pulse generator.

V<sub>EXT</sub> = Test voltage for switching times.

Fig 8. Load circuitry for switching times

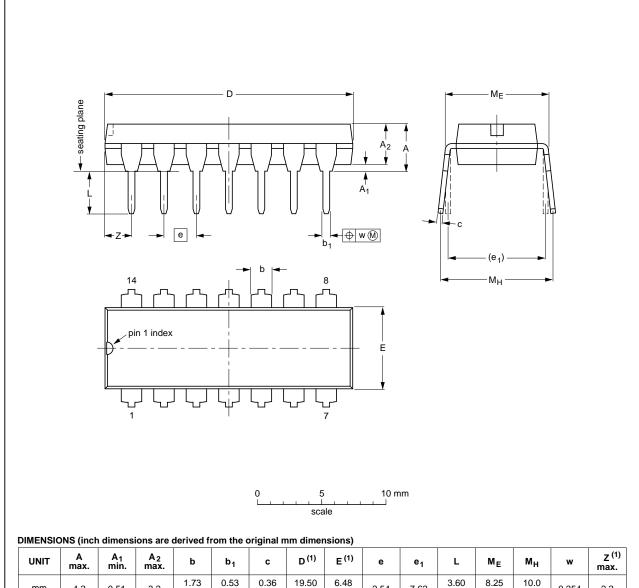
Table 8. Test data

Input	Load		V <sub>EXT</sub>					
$V_{l}$	fı	t <sub>W</sub>	t <sub>r</sub> , t <sub>f</sub> C <sub>L</sub> R <sub>L</sub>		t <sub>PHL</sub> , t <sub>PLH</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	t <sub>PZL</sub> , t <sub>PLZ</sub>	
3.0 V	1 MHz	500 ns	≤ 2.5 ns	50 pF	500 Ω	open	open	7.0 V

# 12. Package outline

DIP14: plastic dual in-line package; 14 leads (300 mil)

SOT27-1



UNIT	A max.	A <sub>1</sub> min.	A <sub>2</sub> max.	b	b <sub>1</sub>	С	D <sup>(1)</sup>	E <sup>(1)</sup>	е	e <sub>1</sub>	L	ME	Мн	w	Z <sup>(1)</sup> max.
mm	4.2	0.51	3.2	1.73 1.13	0.53 0.38	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	2.2
inches	0.17	0.02	0.13	0.068 0.044	0.021 0.015	0.014 0.009	0.77 0.73	0.26 0.24	0.1	0.3	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.087

#### Note

1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

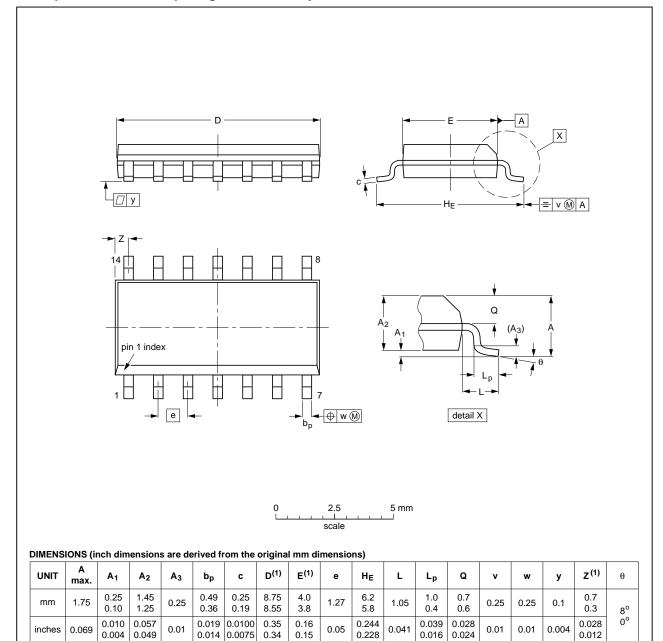
OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT27-1	050G04	MO-001	SC-501-14		<del>99-12-27</del> 03-02-13	

Package outline SOT27-1 (DIP14) Fig 9.

74ABT125

#### SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



#### Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION		REFER	EUROPEAN	ISSUE DATE		
	IEC	JEDEC	JEITA		PROJECTION	1330E DATE
SOT108-1	076E06	MS-012				<del>99-12-27</del> 03-02-19

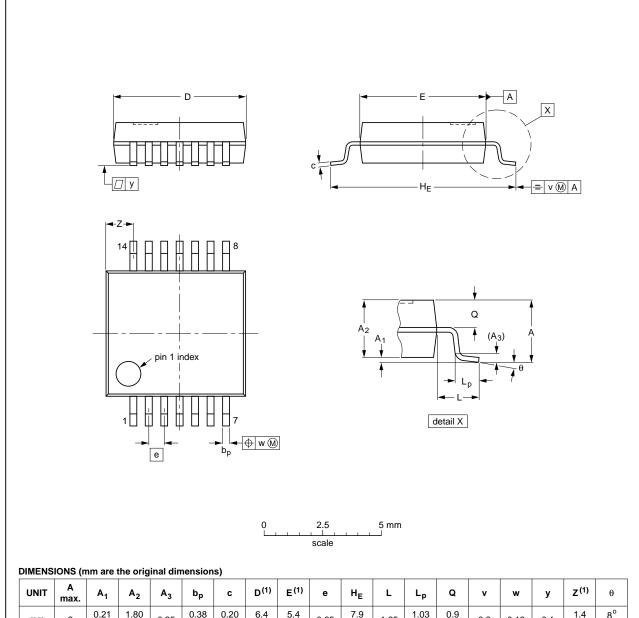
Fig 10. Package outline SOT108-1 (SO14)

4ABT125

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SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	bp	С	D <sup>(1)</sup>	E <sup>(1)</sup>	е	HE	L	Lp	Q	v	w	у	Z <sup>(1)</sup>	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.4 0.9	8° 0°

#### Note

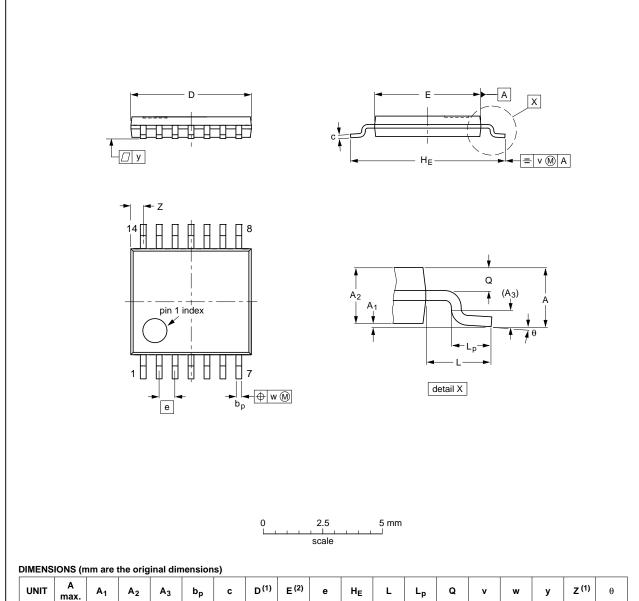
1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

	OUTLINE		REFER	EUROPEAN	ISSUE DATE			
	VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
	SOT337-1		MO-150				<del>99-12-27</del> 03-02-19	
_						•		

Fig 11. Package outline SOT337-1 (SSOP14)

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	bp	С	D <sup>(1)</sup>	E (2)	е	HE	L	Lp	Q	v	w	у	Z <sup>(1)</sup>	θ	1
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°	

#### Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	13302 DATE	
SOT402-1		MO-153				<del>99-12-27</del> 03-02-18	

Fig 12. Package outline SOT402-1 (TSSOP14)

74ABT12

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DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm SOT762-1

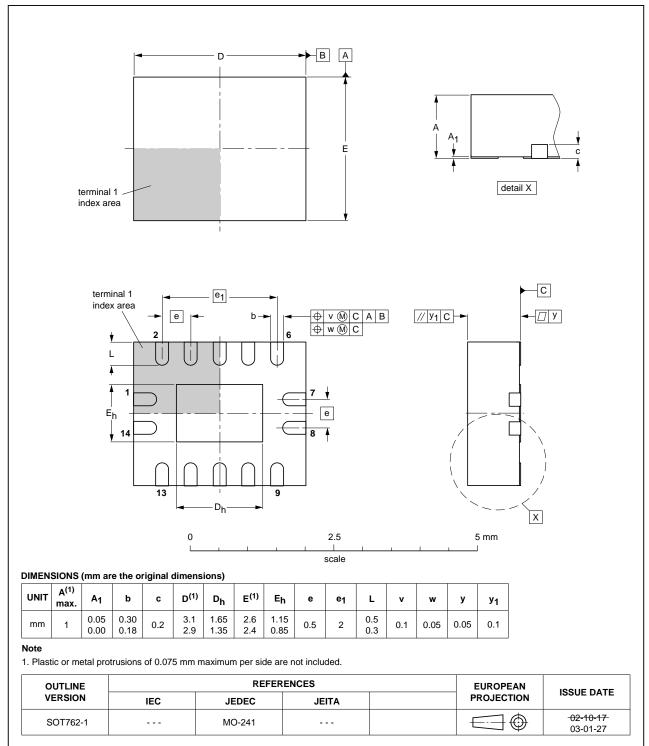


Fig 13. Package outline SOT762-1 (DHVQFN14)

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## 13. Abbreviations

#### Table 9. Abbreviations

Acronym	Description
BiCMOS	BipolarCMOS
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model

# 14. Revision history

#### Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74ABT125 v.6	20111103	Product data sheet	-	74ABT125 v.5
Modifications:	<ul> <li>Legal pages</li> </ul>	updated		
74ABT125 v.5	20101124	Product data sheet	-	74ABT125 v.4
74ABT125 v.4	20100427	Product data sheet	-	74ABT125 v.3
74ABT125 v.3	20080429	Product data sheet	-	74ABT125 v.2
74ABT125 v.2	19980116	Product specification	-	74ABT125 v.1
74ABT125 v.1	19960305	-	-	-

Quad buffer; 3-state

### 15. Legal information

#### 15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.nxp.com">http://www.nxp.com</a>.

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